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April 2015

# FDP083N15A

## N-Channel PowerTrench<sup>®</sup> MOSFET

150 V, 117 A, 8.3 mΩ

### Features

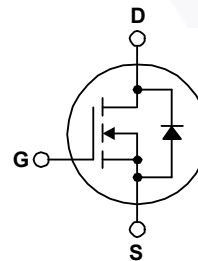
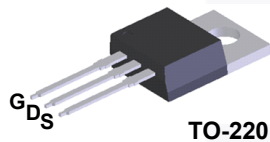
- $R_{DS(on)} = 6.85 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 75 \text{ A}$
- Fast Switching Speed
- Low Gate Charge,  $Q_G = 64.5 \text{ nC}$  (Typ.)
- High Performance Trench Technology for Extremely Low  $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

### Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's PowerTrench<sup>®</sup> process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

### Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Micro Solar Inverter



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FDP083N15A_F102	Unit
$V_{DSS}$	Drain to Source Voltage	150	V
$V_{GSS}$	Gate to Source Voltage	- DC	$\pm 20$
		- AC ( $f > 1 \text{ Hz}$ )	$\pm 30$
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ , Silicon Limited)	117
		- Continuous ( $T_C = 100^\circ\text{C}$ , Silicon Limited)	83
$I_{DM}$	Drain Current	- Pulsed (Note 1)	468
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	542
$dv/dt$	Peak Diode Recovery $dv/dt$	(Note 3)	6
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	294
		- Derate Above $25^\circ\text{C}$	1.96
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FDP083N15A_F102	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.51	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

FDP083N15A — N-Channel PowerTrench<sup>®</sup> MOSFET

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP083N15A_F102	FDP083N15A	TO-220	Tube	N/A	N/A	50 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}, T_C = 25^\circ\text{C}$	150	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.08	-	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 120 \text{ V}, T_C = 150^\circ\text{C}$	-	-	1 500	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 75 \text{ A}$	-	6.85	8.30	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_D = 75 \text{ A}$	-	139	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	-	4645	6040	pF
$C_{oss}$	Output Capacitance		-	1445	1880	pF
$C_{rss}$	Reverse Transfer Capacitance		-	100	-	pF
$C_{iss}$	Input Capacitance	$V_{DS} = 7.5 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	-	4570	6040	pF
$C_{oss}$	Output Capacitance		-	460	1880	pF
$C_{rss}$	Reverse Transfer Capacitance		-	20	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 120 \text{ V}, I_D = 75 \text{ A},$ $V_{GS} = 10 \text{ V}$	-	64.5	84	nC
$Q_{gs}$	Gate to Source Gate Charge		-	19.1	-	nC
$Q_{gs2}$	Gate Charge Threshold to Plateau		-	8.7	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		(Note 4)	-	13.5	-
ESR	Equivalent Series Resistance(G-S)	$f = 1 \text{ MHz}$	-	2.5	-	$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75 \text{ V}, I_D = 75 \text{ A},$ $V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$	-	22	54	ns
$t_r$	Turn-On Rise Time		-	58	126	ns
$t_{d(off)}$	Turn-Off Delay Time		-	61	132	ns
$t_f$	Turn-Off Fall Time		(Note 4)	-	26	62

### Drain-Source Diode Characteristics

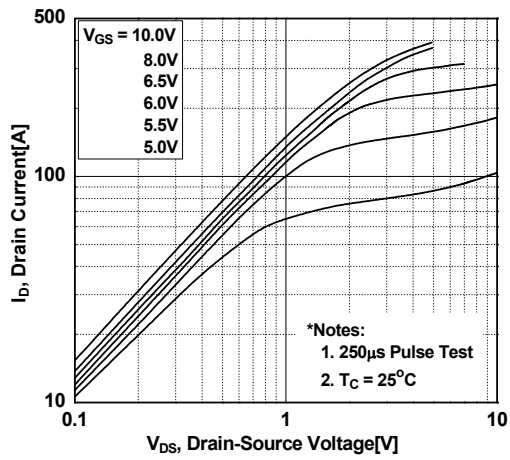
$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	117	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	468	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 75 \text{ A}$	-	-	1.25	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{SD} = 75 \text{ A},$ $di_F/dt = 100 \text{ A}/\mu\text{s}$	-	96	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	268	-	nC

#### Notes:

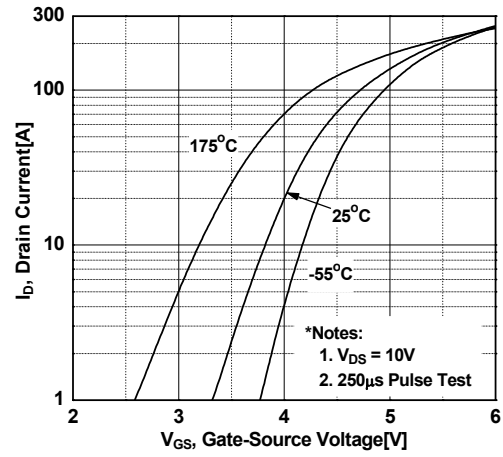
1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. Starting  $T_J = 25^\circ\text{C}$ ,  $L = 3 \text{ mH}$ ,  $I_{SD} = 19 \text{ A}$ .
3.  $I_{SD} \leq 75 \text{ A}$ ,  $di/dt \leq 200 \text{ A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

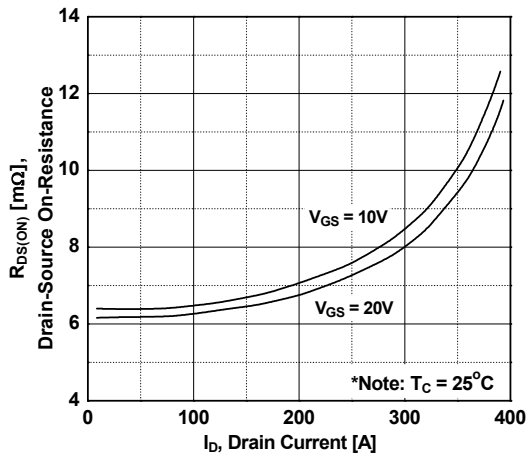
**Figure 1. On-Region Characteristics**



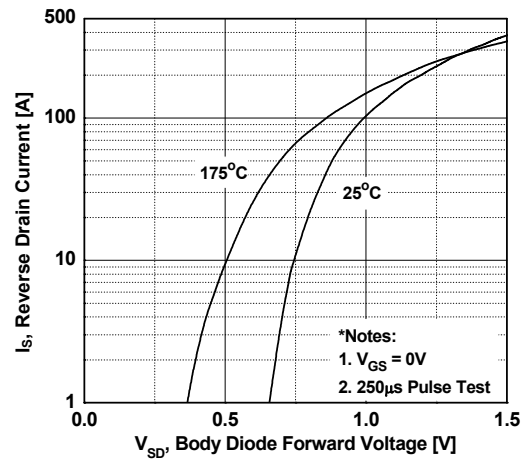
**Figure 2. Transfer Characteristics**



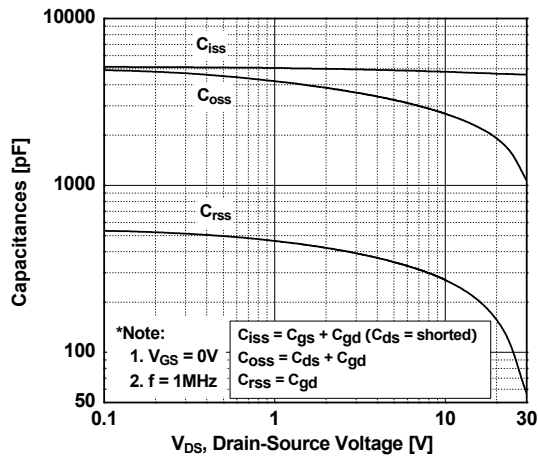
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



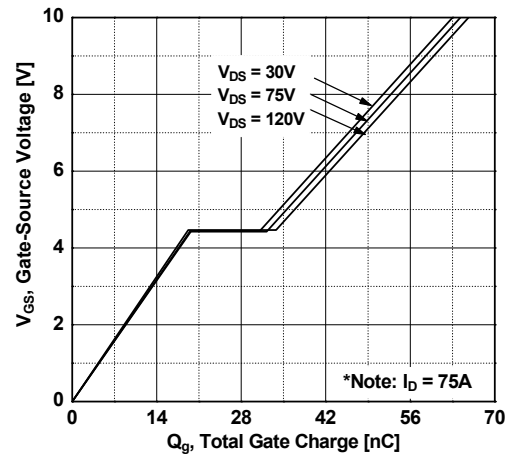
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

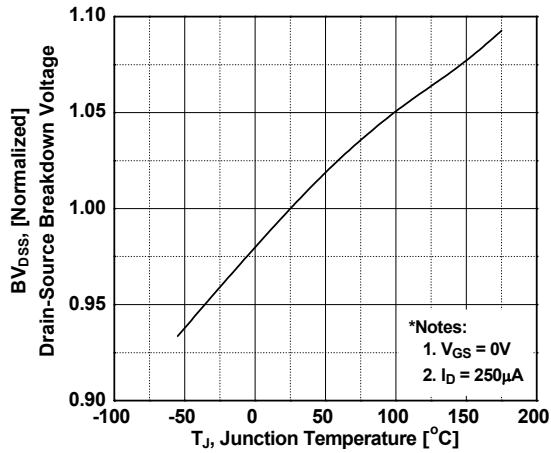


**Figure 6. Gate Charge Characteristics**

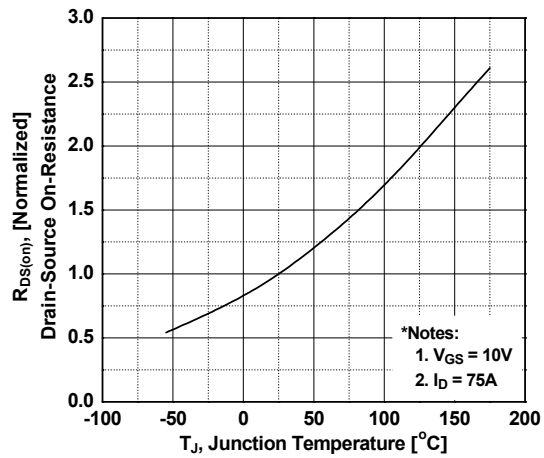


**Typical Performance Characteristics** (Continued)

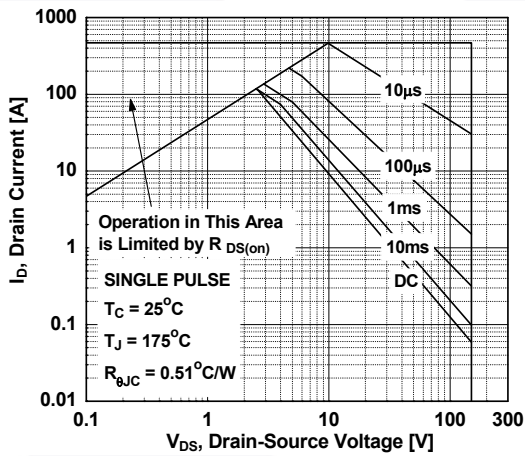
**Figure 7. Breakdown Voltage Variation vs. Temperature**



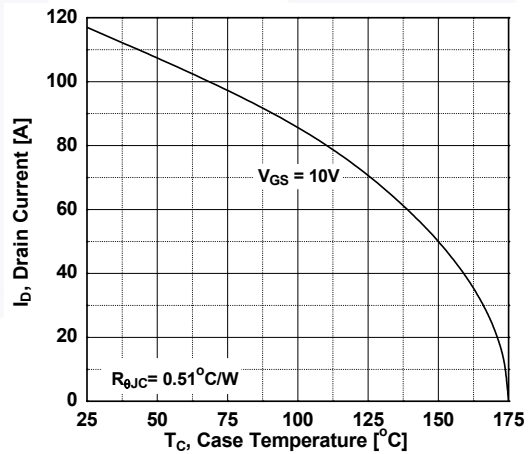
**Figure 8. On-Resistance Variation vs. Temperature**



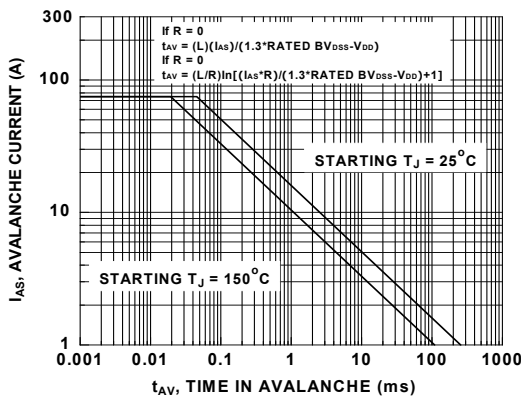
**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**

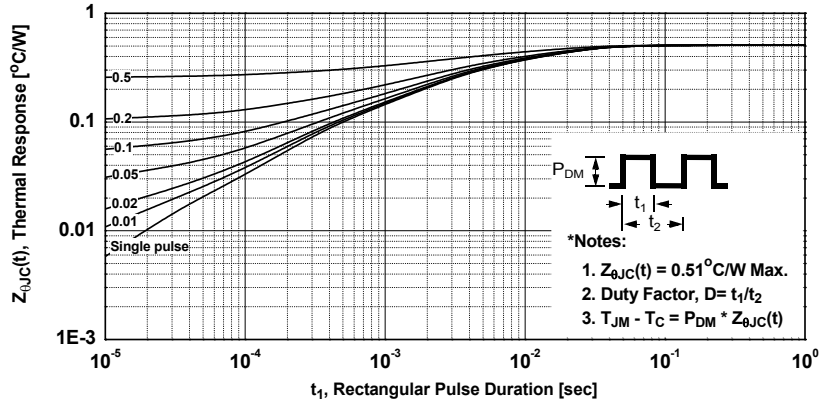


**Figure 11. Unclamped Inductive Switching Capability**



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



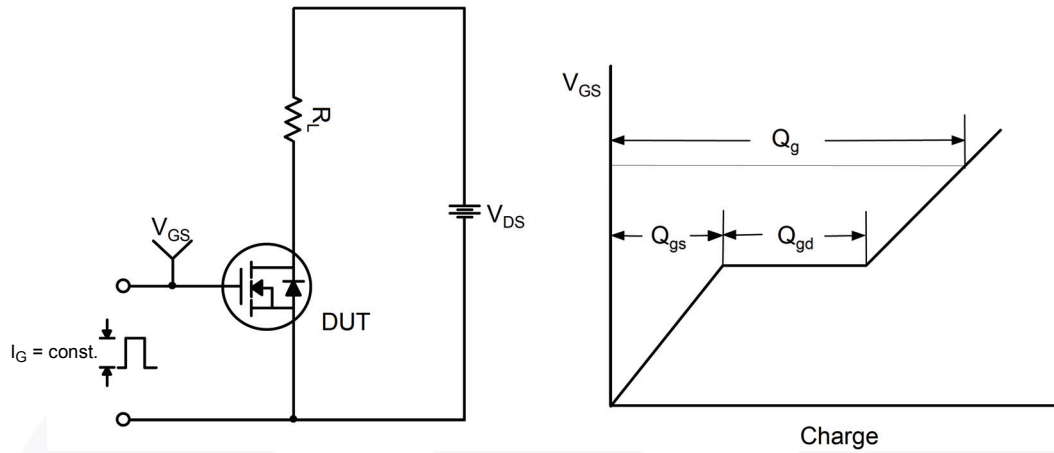


Figure 13. Gate Charge Test Circuit & Waveform

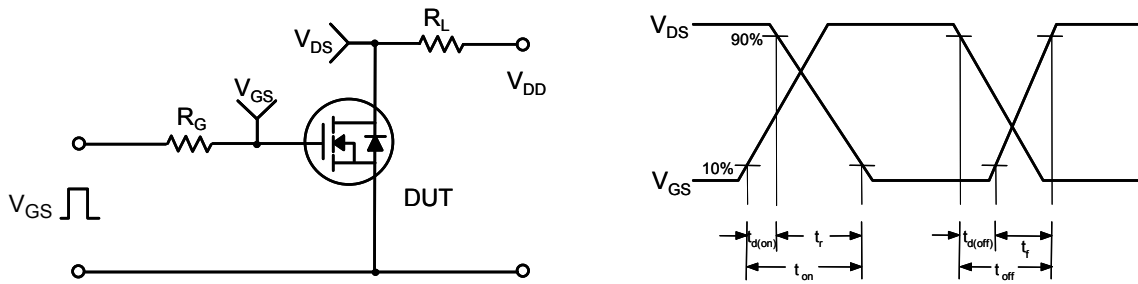


Figure 14. Resistive Switching Test Circuit & Waveforms

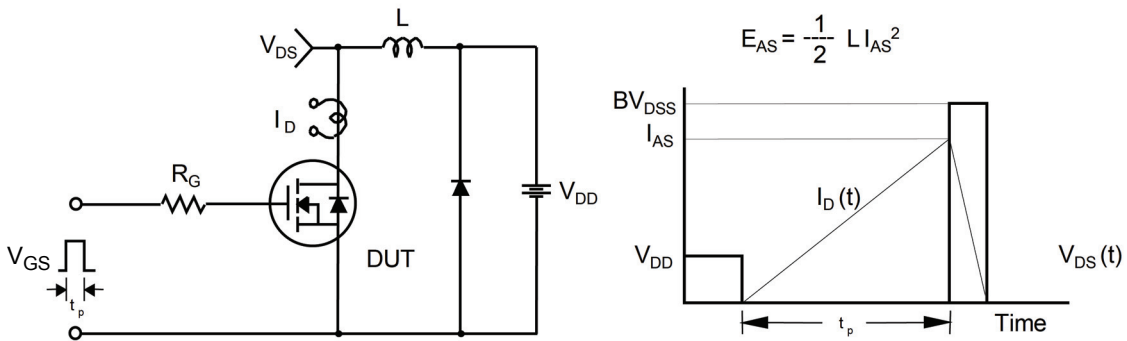


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

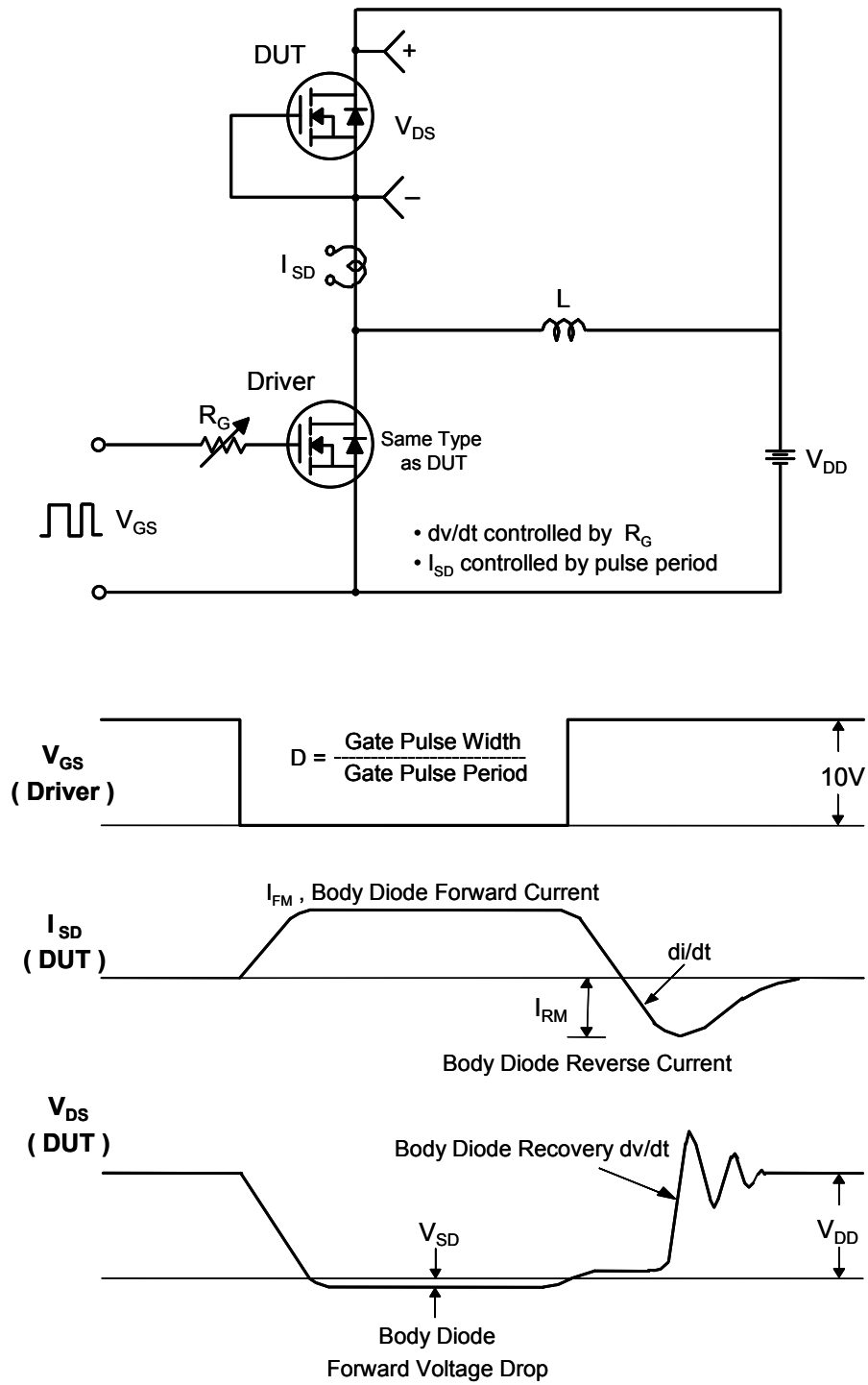
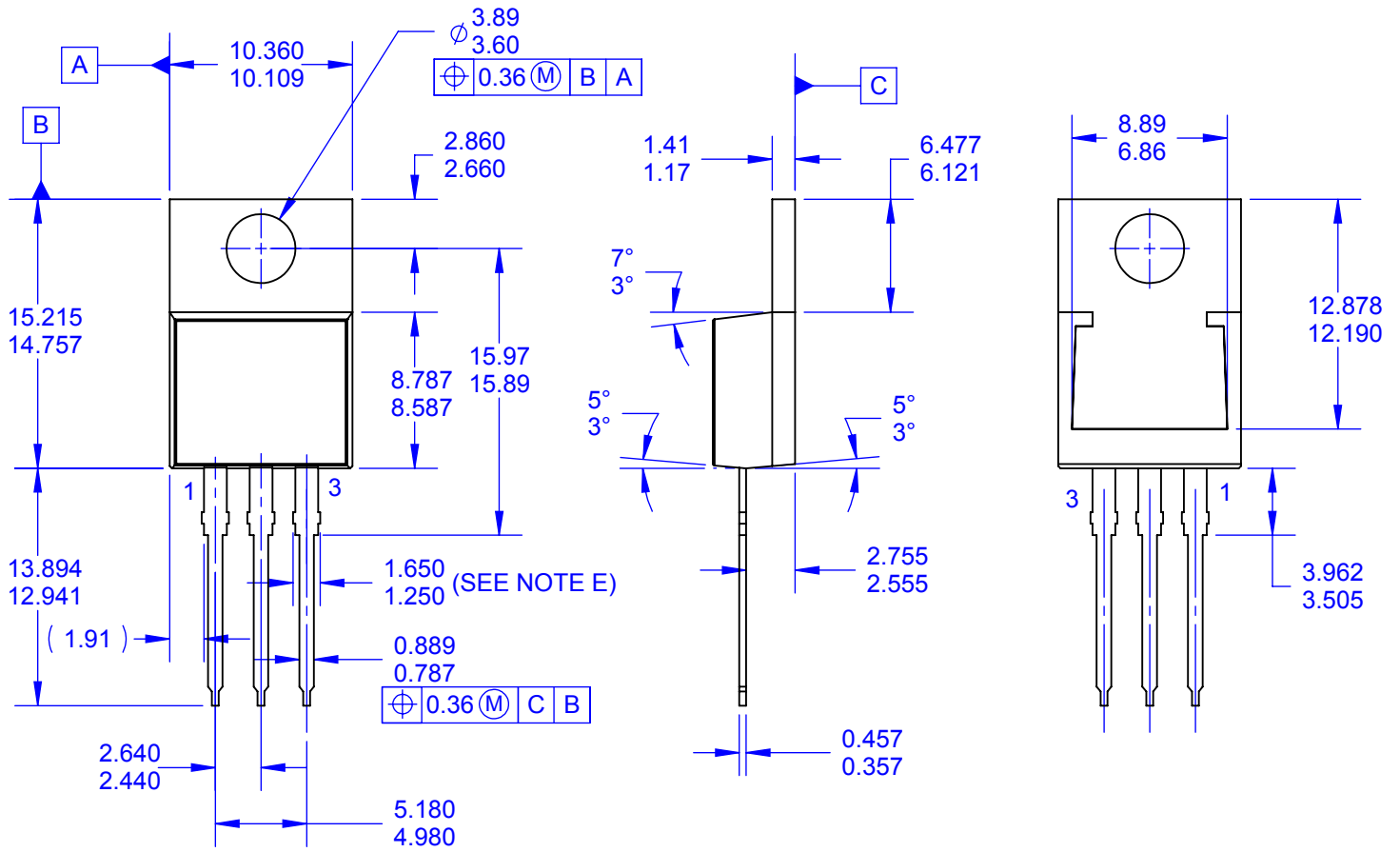


Figure 16. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms





**NOTES:**

- A. PACKAGE REFERENCE: JEDEC TO220 VARIATION AB
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. MAX WIDTH FOR F102 DEVICE = 1.35mm.
- F. DRAWING FILE NAME: TO220T03REV4.
- G. FAIRCHILD SEMICONDUCTOR.

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